

N-channel TrenchMOS logic level FET Rev. 3 — 8 February 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### **1.3 Applications**

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1.	1. Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	75	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	aracteristics						
$R_{DSon}$	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	2	2.4	mΩ
	resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \overline{Figure \ 11}; \\ \text{see } \overline{Figure \ 12} \end{array}$		-	2.4	2.8	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 30  \text{V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 5  \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	2.3	J
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 24 V; T_j = 25 °C;$ see Figure 13	-	35	-	nC

[1] Continuous current is limited by package.

#### **Pinning information** 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

#### **Ordering information** 3.

#### Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
BUK962R8-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 3</u> ;	<u>[1]</u> -	237	А
		see Figure 1	[2] _	75	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>	[2] _	75	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>	-	950	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	300	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	[3] _	75	А
			<u>[1]</u> -	237	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	950	А
Avalanche ru	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped	-	2.3	J

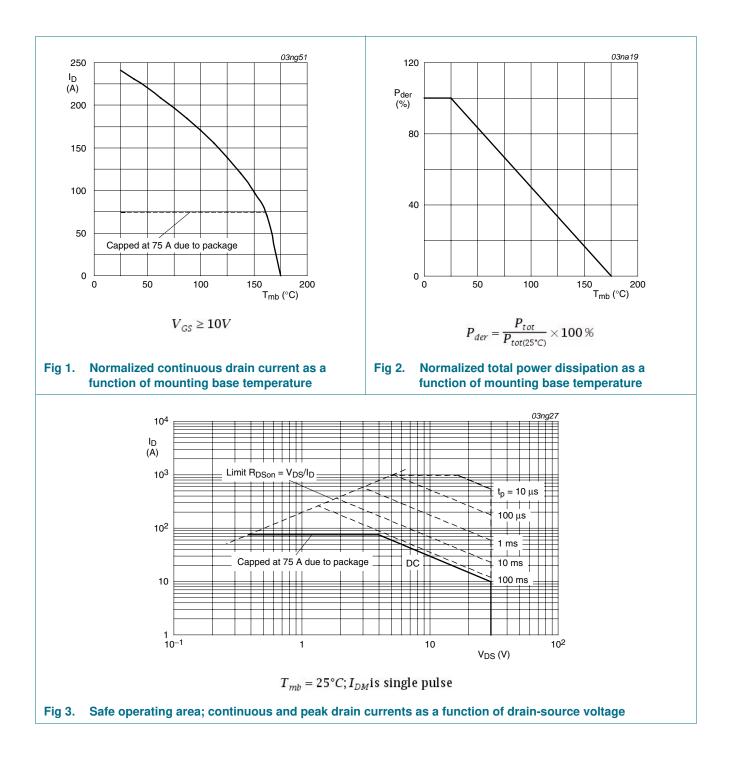
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

[3] Continuous current is limited by package.

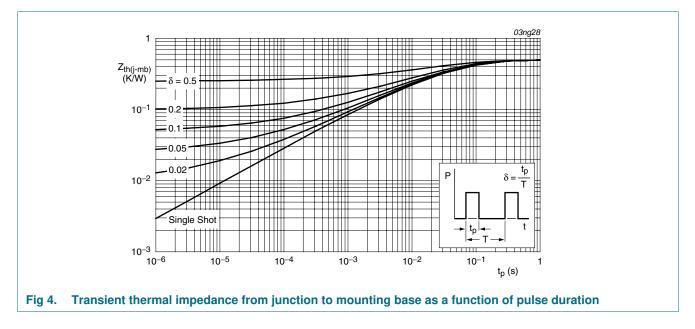
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#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



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## 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	30	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	27	-	-	V
G.G()	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	1.1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub> gate leakage current	V <sub>GS</sub> = 15 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA	
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 175 \text{ °C};$ see Figure 11; see Figure 12	-	-	5.3	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C	-	2	2.4	mΩ
	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	3	mΩ	
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	2.4	2.8	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$	-	89	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	22	-	nC
Q <sub>GD</sub>	gate-drain charge		-	35	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	7640	10185	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	1600	1920	pF
C <sub>rss</sub>	reverse transfer capacitance		-	735	1006	pF
d(on)	turn-on delay time	$V_{DS} = 30 \ V; \ R_L = 1.2 \ \Omega; \ V_{GS} = 5 \ V;$	-	71	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	222	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	260	-	ns
t <sub>f</sub>	fall time		-	195	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

Symbol

# BUK962R8-30B

Unit

Max

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Тур

Min

Source-dra	vin diada							
						0.05	1.0	
/ <sub>SD</sub>	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0$ see <u>Figure 15</u>			-	0.85	1.2	V
rr	reverse recovery time	$I_{\rm S} = 20 \text{ A}; dI_{\rm S}/dt = -$			-	109	-	ns
λr	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> =	20 V; $I_j = 25  {}^{\circ}C$		-	171	-	nC
300	_	03ng24	5				03ng23	
I <sub>D</sub> (A) 10			R <sub>DSon</sub>					
250 —	V <sub>GS</sub> = 3.8	3 V	(mΩ)					
		3.6						
200 -			4					
		3.4						
150 —		3.2						
100								
100 -		3	3					
50		2.8						
		2.6						
<sub>0</sub> ک		2.4	2					
0				_		10	15	
0	2 4 6	8 10 V <sub>DS</sub> (V)	- 0	5		10 V <sub>G</sub>	15 S (V)	
0		V <sub>DS</sub> (V)	0			V <sub>G</sub>	<sub>S</sub> (V)	
0	2   4   6 $T_j = 25^{\circ}C; t_p = 300\mu$	V <sub>DS</sub> (V)	0	5 T <sub>j</sub> = 25	°C;I <sub>D</sub> =	V <sub>G</sub>	<sub>S</sub> (V)	
	$T_j = 25^{\circ}C; t_p = 300\mu$	V <sub>DS</sub> (V) <i>1S</i>	0	<i>T</i> <sub>j</sub> = 25		V <sub>G</sub> = 25A	<sub>S</sub> (V)	
Fig 5. Ou		V <sub>DS</sub> (V) <i>IS</i>	Fig 6. Drain-s		state re	v <sub>G</sub> = 25A esistanc	<sub>s</sub> (V) <b>e as a f</b> u	
Fig 5. Ou fui	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V <sub>DS</sub> (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or fur <sup>10−1</sup> ⊨	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V <sub>DS</sub> (V) <i>IS</i> n current as a	Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s</sub> (V) <b>e as a f</b> u	
Fig 5. Ou fui	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V <sub>DS</sub> (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or fur 10 <sup>-1</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V <sub>DS</sub> (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s of gate-	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Ou fun 10 <sup>-1</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or fur 10 <sup>-1</sup> ID (A) 10 <sup>-2</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Ou fun 10 <sup>-1</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	Fig 6.         Drain-s of gate           grs         0           125         100	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or fur 10 <sup>-1</sup> (A) 10 <sup>-2</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or fur 10 <sup>-1</sup> ID (A) 10 <sup>-2</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	0 Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
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Fig 5. Or ful 10 <sup>-1</sup> (A) 10 <sup>-2</sup> 10 <sup>-3</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	0 Fig 6. Drain-s of gate	$T_j = 25$	state re	v <sub>G</sub> = 25A esistanc	<sub>s (V)</sub> e as a fu values	
Fig 5. Or ful 10 <sup>-1</sup> (A) 10 <sup>-2</sup> 10 <sup>-3</sup> 10 <sup>-4</sup> 10 <sup>-5</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> accurrent as a age; typical values 03ng53 / / max	Fig 6. Drain-s of gate (S) 125 100 75 50 25 0	T <sub>j</sub> = 25	state re ltage; t	v <sub>G</sub> = 25A esistanc typical v	e as a fu ralues 03ng21	unction
Fig 5. Or ful 10 <sup>-1</sup> (A) 10 <sup>-2</sup> 10 <sup>-3</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	V <sub>G</sub> esistance typical v	<sub>s (V)</sub> e as a fu values	unction
Fig 5. Or fur 10 <sup>-1</sup> (A) 10 <sup>-2</sup> 10 <sup>-3</sup> 10 <sup>-4</sup> 10 <sup>-5</sup>	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V)	Fig 6. Drain-s of gate (S) 125 100 75 50 25 0	T <sub>j</sub> = 25	40	v <sub>G</sub> esistance e	e as a fu values 03ng21	unction
Fig 5. Or full $10^{-1}$ $10^{-1}$ $(A)$ $10^{-2}$ $10^{-3}$ $10^{-4}$ $10^{-5}$ $10^{-6}$ $0$	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V <sub>DS</sub> (V) <i>IS</i> <b>age; typical values</b>	Fig 6. Drain-s of gate	T <sub>j</sub> = 25	40	v <sub>G</sub> = 25A esistance typical v	e as a fu ralues 03ng21	unction

#### Table 6. Characteristics ...continued

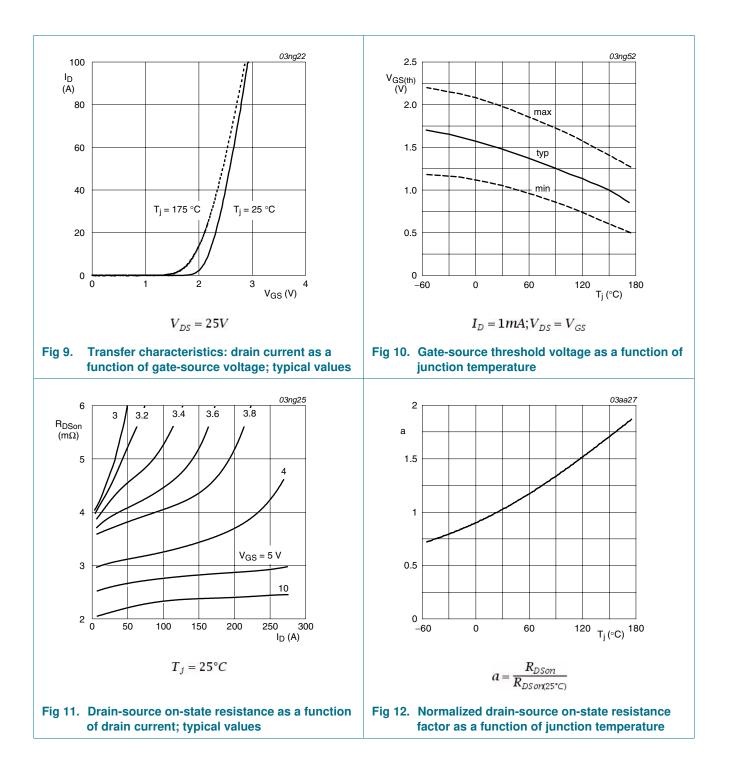
Parameter

Conditions

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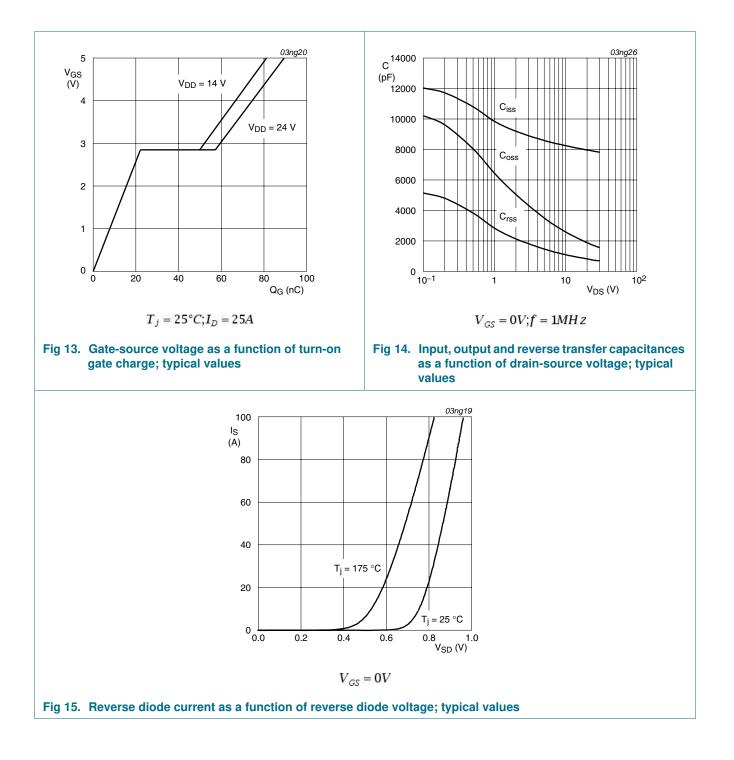
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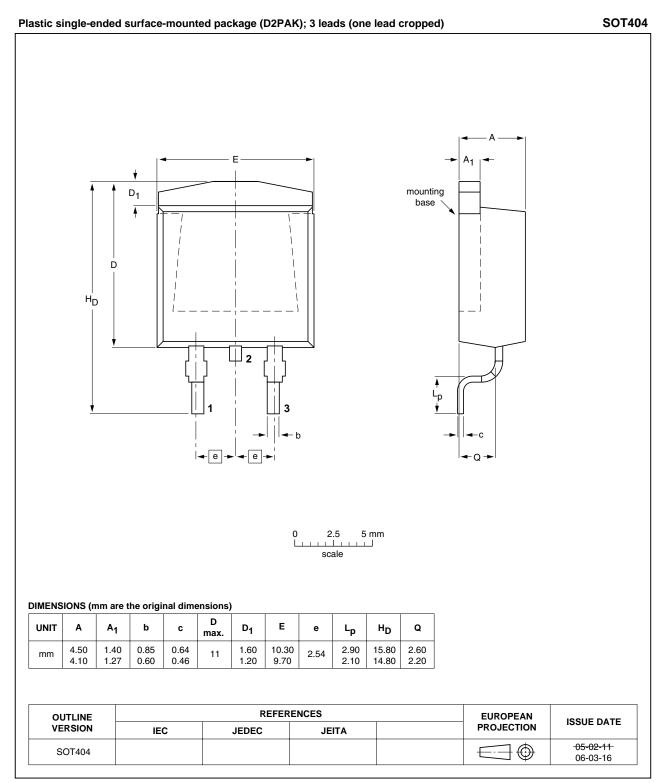
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#### N-channel TrenchMOS logic level FET



#### N-channel TrenchMOS logic level FET

## 7. Package outline



#### Fig 16. Package outline SOT404 (D2PAK)

All information provided in this document is subject to legal disclaimers.

BUK962R8-30B

## 8. Revision history

Release date	<b>.</b>		
	Data sheet status	Change notice	Supersedes
20110208	Product data sheet	-	BUK95_962R8_30B v.2
		n redesigned to co	omply with the new identity
<ul> <li>Legal texts have</li> </ul>	ave been adapted to the	new company na	me where appropriate.
<ul> <li>Type number</li> </ul>	r BUK962R8-30B separa	ted from data she	et BUK95_962R8_30B v.2.
20021014	Product data	-	BUK95_962R8_30B v.1
	<ul> <li>The format o guidelines of</li> <li>Legal texts h</li> <li>Type number</li> </ul>	<ul> <li>The format of this data sheet has been guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the</li> <li>Type number BUK962R8-30B separation</li> </ul>	<ul> <li>The format of this data sheet has been redesigned to conguidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company nare</li> <li>Type number BUK962R8-30B separated from data sheet sheet</li></ul>

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

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### **10. Contact information**

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: <u>salesaddresses@nexperia.com</u>

#### 9.4 Trademarks

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